

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IRFP3077, IIRFP3077

• FEATURES

- Static drain-source on-resistance: RDs(on)≤3.3mΩ
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

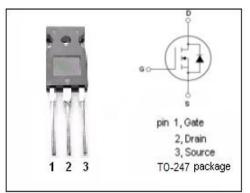
- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched And High Frequency Circuits

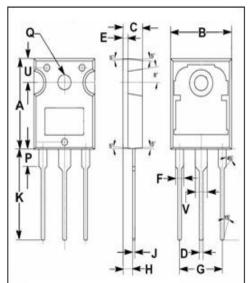
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage	75	V	
V _{GS}	Gate-Source Voltage	±20	V	
ID	Drain Current-Continuous	А		
I _{DM}	Drain Current-Single Pulsed	Pulsed 850		
PD	Total Dissipation @T _c =25°C	issipation @T _c =25°C 340		
Tj	Max. Operating Junction Temperature 175		°C	
T _{stg}	Storage Temperature	-55~175	°C	

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth(j-c)	Channel-to-case thermal resistance	0.44	°C/W
Rth(j-a) Channel-to-ambient thermal resistant		40	°C/W









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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =250 μ A	75			V
V _{GS} (th)	Gate Threshold Voltage	VDS=VGS; I _D =250 µ A	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =75A			3.3	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =100V; V _{GS} = 0V			20	μA
V _{SD}	Diode forward voltage	I _S =75A, V _{GS} = 0V			1.3	V

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